Proposed

RF3802

GaAs HBT PRE-DRIVER AMPLIFIER

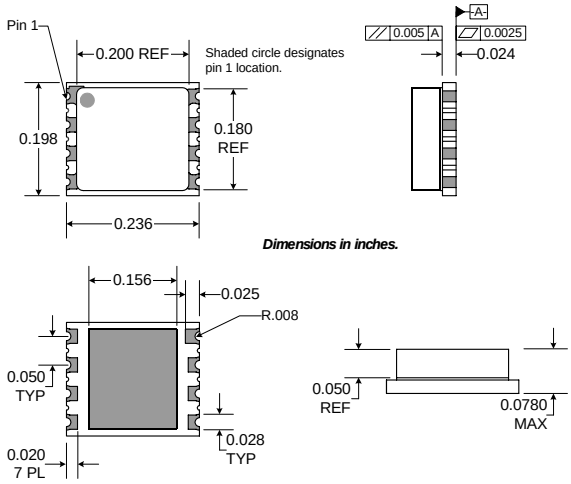
Typical Applications

- GaAs HBT Pre-Driver for Basestation Amplifiers
- Power Amplifier Stage for Commercial Wireless Infrastructure
- Class AB Operation for GSM/EDGE/CDMA Transmitter Applications

Product Description

The RF3802 is specifically designed for wireless infrastructure applications. Using a highly reliable GaAs HBT fabrication process, this high-performance dual-stage amplifier achieves high output power over a broad frequency range. The RF3802 amplifier also provides excellent efficiency and thermal stability through the use of a thermally-enhanced surface-mount AlN package. Ease of integration is accomplished through the incorporation of an optimized evaluation board design provided to achieve proper 50Ω operation. Various evaluation board bias configurations are available to address a broad range of wireless infrastructure applications:

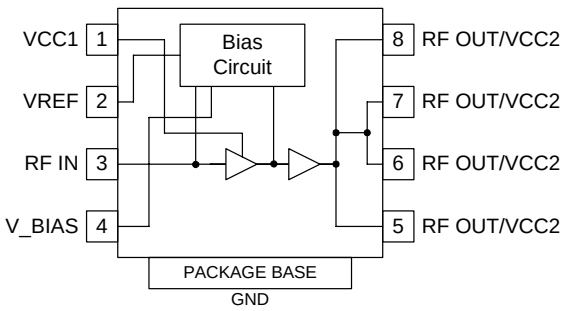
- AMPS/GSM850/EDGE850
- GSM900/EDGE900
- IS-95/CDMA2000/AMPS



Package Style: AIN

Optimum Technology Matching® Applied

- ☐ Si BJT
- ☑ GaAs HBT
- ☐ GaAs MESFET
- ☐ Si Bi-CMOS
- ☐ SiGe HBT
- ☐ Si CMOS
- ☐ InGaP/HBT
- ☐ GaN HEMT
- ☐ SiGe Bi-CMOS



Functional Block Diagram

Features

- 5W Output Power
- High Linearity
- 35% Power-Added Efficiency
- AlN Packaging
- Broadband Platform Design Approach

Ordering Information

RF3802	GaAs HBT Pre-Driver Amplifier
RF3802PCBA-410	Fully Assembled Evaluation Board - GSM850
RF3802PCBA-411	Fully Assembled Evaluation Board - GSM900

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